



UTT120N04

Preliminary

Power MOSFET

**120A, 40V N-CHANNEL
POWER MOSFET**

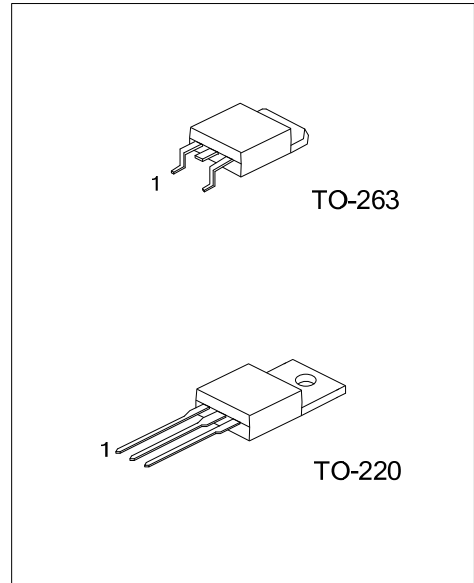
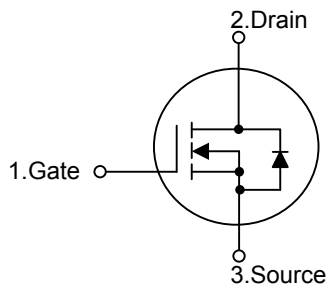
■ DESCRIPTION

The UTC **UTT120N04** is an N-channel enhancement mode Power FET, it uses UTC's advanced technology to provide customers a minimum on-state resistance and high switching speed.

■ FEATURES

- * $R_{DS(ON)} < 3.8m\Omega @ V_{GS}=10V, I_D=60A$
- * High switching speed
- * Improved dv/dt capability

■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UTT120N04L-TA3-T	UTT120N04G-TA3-T	TO-220	G	D	S	Tube
UTT120N04L-TQ2-T	UTT120N04G-TQ2-T	TO-263	G	D	S	Tube
UTT120N04L-TQ2-R	UTT120N04G-TQ2-R	TO-263	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>UTT120N04L-TA3-T</p> <p>(1) Packing Type</p> <p>(2) Package Type</p> <p>(3) Lead Free</p>	<p>(1) T: Tube, R: Tape Reel</p> <p>(2) TA3: TO-220, TQ2: TO-263</p> <p>(3) L: Lead Free, G: Halogen Free</p>
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■ ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	40	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current	Continuous	I_D	120	A
	Pulsed	I_{DM}	480	A
Avalanche Energy	Single Pulsed	E_{AS}	541.5	mJ
Power Dissipation		P_D	100	W
Junction Temperature		T_J	+150	$^{\circ}C$
Storage Temperature Range		T_{STG}	-55~+150	$^{\circ}C$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL CHARACTERISTICS

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient		θ_{JA}	62.5	$^{\circ}C/W$
Junction to Case		θ_{JC}	1.5	$^{\circ}C/W$

■ ELECTRICAL CHARACTERISTICS

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage		BV_{DSS}	$I_D=250\mu A, V_{GS}=0V$	40			V	
Drain-Source Leakage Current		I_{DSS}	$V_{DS}=32V$			10	μA	
Gate-Source Leakage Current	Forward	I_{GSS}	$V_{GS}=+20V, V_{DS}=0V$			+100	nA	
	Reverse		$V_{GS}=-20V, V_{DS}=0V$			-100	nA	
ON CHARACTERISTICS								
Gate Threshold Voltage		$V_{GS(TH)}$	$I_D=250\mu A$	1		3	V	
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	$V_{GS}=10V, I_D=60A$			3.8	m Ω	
DYNAMIC PARAMETERS								
Input Capacitance		C_{ISS}	$V_{DS}=25V, V_{GS}=0V, f=1MHz$		2890		pF	
Output Capacitance		C_{OSS}				575		pF
Reverse Transfer Capacitance		C_{RSS}				310		pF
SWITCHING PARAMETERS								
Total Gate Charge		Q_G	$V_{DD}=30V, V_{GS}=10V, I_D=1A, I_G=100\mu A$		160	200	nC	
Gate to Source Charge		Q_{GS}				35		nC
Gate to Drain Charge		Q_{GD}				42	60	nC
Turn-ON Delay Time		$t_{D(ON)}$	$V_{DD}=30V, I_D=0.5A, R_G=25\Omega, V_{GS}=0\sim 10V$		17		ns	
Rise Time		t_R				140		ns
Turn-OFF Delay Time		$t_{D(OFF)}$				72		ns
Fall-Time		t_F				26		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS								
Maximum Body-Diode Continuous Current		I_S				120	A	
Maximum Body-Diode Pulsed Current		I_{SM}				480	A	
Drain-Source Diode Forward Voltage		V_{SD}	$I_S=120A$			1.28	V	

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